

# Mathias M Schubert

## List of Publications by Year in descending order

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349  
papers

9,947  
citations

61687

45  
h-index

64407

83  
g-index

356  
all docs

356  
docs citations

356  
times ranked

9566  
citing authors

#	ARTICLE	IF	CITATIONS
1	dielectric functions and Brillouin zone center phonons of $\text{O}_3$ compared to $\text{O}_2$ . <i>Physical Review Materials</i> , 2022, 120, .	0.9	10
2	Linear strain and stress potential parameters for the three fundamental band to band transitions in $\text{Ga}_2\text{O}_3$ . <i>Applied Physics Letters</i> , 2022, 120, .	1.5	3
3	Hyperbolic shear polaritons in low-symmetry crystals. <i>Nature</i> , 2022, 602, 595-600.	13.7	78
4	Terahertz electron paramagnetic resonance generalized spectroscopic ellipsometry: The magnetic response of the nitrogen defect in 4H-SiC. <i>Applied Physics Letters</i> , 2022, 120, .	1.5	8
5	Infrared-active phonon modes and static dielectric constants in $(\text{Al}_{1-x}\text{Ga}_x)_2\text{O}_3$ (0.18 ≤ x ≤ 0.54) alloys. <i>Applied Physics Letters</i> , 2022, 120, .	1.5	4
6	Elevated temperature spectroscopic ellipsometry analysis of the dielectric function, exciton, band-to-band transition, and high-frequency dielectric constant properties for single-crystal $\text{ZnGa}_2\text{O}_4$ . <i>Applied Physics Letters</i> , 2022, 120, .	1.5	4
7	A review of band structure and material properties of transparent conducting and semiconducting oxides: $\text{Ga}_2\text{O}_3$ , $\text{Al}_2\text{O}_3$ , $\text{In}_2\text{O}_3$ , $\text{ZnO}$ , $\text{SnO}_2$ , $\text{CdO}$ , $\text{NiO}$ , $\text{CuO}$ , and $\text{Sc}_2\text{O}_3$ . <i>Applied Physics Reviews</i> , 2022, 9, .	5.5	124
8	Epitaxial growth of $\text{Ga}_2\text{O}_3$ by hot-wall MOCVD. <i>AIP Advances</i> , 2022, 12, .	0.6	17
9	Enhancement of 2DEG effective mass in $\text{AlN}/\text{Al}_0.78\text{Ga}_0.22\text{N}$ high electron mobility transistor structure determined by THz optical Hall effect. <i>Applied Physics Letters</i> , 2022, 120, .	1.5	3
10	Resolving mobility anisotropy in quasi-free-standing epitaxial graphene by terahertz optical Hall effect. <i>Carbon</i> , 2021, 172, 248-259.	5.4	4
11	Broadband Enhanced Chirality with Tunable Response in Hybrid Plasmonic Helical Metamaterials. <i>Advanced Functional Materials</i> , 2021, 31, 2010329.	7.8	26
12	Anisotropic dielectric functions, band-to-band transitions, and critical points in $\text{Ga}_2\text{O}_3$ . <i>Applied Physics Letters</i> , 2021, 118, .	1.5	19
13	Zinc gallate spinel dielectric function, band-to-band transitions, and $\Gamma^c$ -point effective mass parameters. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	9
14	Helical Nanostructures: Broadband Enhanced Chirality with Tunable Response in Hybrid Plasmonic Helical Metamaterials ( <i>Adv. Funct. Mater.</i> 20/2021). <i>Advanced Functional Materials</i> , 2021, 31, 2170143.	7.8	1
15	Optical phonon modes, static and high-frequency dielectric constants, and effective electron mass parameter in cubic $\text{In}_2\text{O}_3$ . <i>Journal of Applied Physics</i> , 2021, 129, .	1.1	11
16	Mueller matrix imaging microscope using dual continuously rotating anisotropic mirrors. <i>Optics Express</i> , 2021, 29, 28704.	1.7	4
17	High-frequency and below bandgap anisotropic dielectric constants in $(\text{Al}_{1-x}\text{Ga}_x)_2\text{O}_3$ (x = 1). <i>Applied Physics Letters</i> , 2021, 119, .	1.5	14
18	Numerical ellipsometry: A method for selecting a near-minimal infrared measurement set for $\Gamma^c$ -gallium oxide. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	0.9	3

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19	Tunable Broadband Enhanced Chirality with Hybrid Helical Metamaterials. , 2021, , .		0
20	Stretchable Thin Film Mechanicalâ€¦Strainâ€¦Gated Switches and Logic Gate Functions Based on a Soft Tunneling Barrier (Adv. Mater. 41/2021). Advanced Materials, 2021, 33, 2170320.	11.1	0
21	Origin of layer decoupling in ordered multilayer graphene grown by high-temperature sublimation on C-face 4H-SiC. APL Materials, 2020, 8, .	2.2	4
22	Precursor-surface interactions revealed during plasma-enhanced atomic layer deposition of metal oxide thin films by in-situ spectroscopic ellipsometry. Scientific Reports, 2020, 10, 10392.	1.6	8
23	Brillouin zone center phonon modes in ZnGa2O4. Applied Physics Letters, 2020, 117, .	1.5	5
24	Tunable cavity-enhanced terahertz frequency-domain optical Hall effect. Review of Scientific Instruments, 2020, 91, 083903.	0.6	11
25	Strain and stress relationships for optical phonon modes in monoclinic crystals with $\hat{\Gamma}^2$ as an example. Physical Review B, 2020, 102, .	1.1	13
26	Infrared-active phonon modes in single-crystal thorium dioxide and uranium dioxide. Journal of Applied Physics, 2020, 127, .	1.1	7
27	Comment on "Characteristics of Multi-photon Absorption in a $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> Single Crystal" [J. Phys. Soc. Jpn. 88, 113701 (2019)]. Journal of the Physical Society of Japan, 2020, 89, 036001.	0.7	0
28	Infrared active phonons in monoclinic lutetium oxyorthosilicate. Journal of Applied Physics, 2020, 127, .	1.1	6
29	Numerical ellipsometry: Methods for selecting measurements and techniques for advanced analysis applied to $\hat{\Gamma}^2$ -gallium oxide. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	3
30	The anisotropic quasi-static permittivity of single-crystal $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> measured by terahertz spectroscopy. Applied Physics Letters, 2020, 117, .	1.5	27
31	Mueller matrix ellipsometer using dual continuously rotating anisotropic mirrors. Optics Letters, 2020, 45, 3541.	1.7	3
32	Phonon Properties. Springer Series in Materials Science, 2020, , 501-534.	0.4	1
33	Visualization of label-free titanium dioxide nanoparticle deposition on surfaces with nanoscale roughness. Environmental Science: Nano, 2019, 6, 248-260.	2.2	5
34	Band-to-band transitions and critical points in the near-infrared to vacuum ultraviolet dielectric functions of single crystal urania and thoria. Applied Physics Letters, 2019, 114, .	1.5	13
35	Dielectric function tensor (1.5 eV to 9.0 eV), anisotropy, and band to band transitions of monoclinic $\hat{\Gamma}^2$ -(Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> (x=0.21) films. Applied Physics Letters, 2019, 114, .	1.5	25
36	Lattice dynamics of orthorhombic NdGaO <sub>3</sub> . Physical Review B, 2019, 99, .		

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37	On the anomalous optical conductivity dispersion of electrically conducting polymers: ultra-wide spectral range ellipsometry combined with a Drude-Lorentz model. <i>Journal of Materials Chemistry C</i> , 2019, 7, 4350-4362.	2.7	36
38	Longitudinal phonon plasmon mode coupling in $\text{In}_2\text{-Ga}_2\text{O}_3$ . <i>Applied Physics Letters</i> , 2019, 114, .	1.5	21
39	Deposition of titanium dioxide nanoparticles onto engineered rough surfaces with controlled heights and properties. <i>Colloids and Surfaces A: Physicochemical and Engineering Aspects</i> , 2019, 571, 125-133.	2.3	8
40	Electromagnon excitation in cupric oxide measured by Fabry-Pérot enhanced terahertz Mueller matrix ellipsometry. <i>Scientific Reports</i> , 2019, 9, 1353.	1.6	6
41	Free Polyethylenimine Enhances Substrate-Mediated Gene Delivery on Titanium Substrates Modified With RGD-Functionalized Poly(acrylic acid) Brushes. <i>Frontiers in Chemistry</i> , 2019, 7, 51.	1.8	6
42	Phonon order and reststrahlen bands of polar vibrations in crystals with monoclinic symmetry. <i>Physical Review B</i> , 2019, 99, .	1.1	13
43	Tunable plasmonic resonances in Si-Au slanted columnar heterostructure thin films. <i>Scientific Reports</i> , 2019, 9, 71.	1.6	12
44	Walk the Talk: Financial Fairness in European Club Football. <i>Sport, Ethics and Philosophy</i> , 2019, 13, 33-48.	0.4	9
45	Electron effective mass in $\text{In}_{0.33}\text{Ga}_{0.67}\text{N}$ determined by mid-infrared optical Hall effect. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	6
46	Financial Doping and Financial Fair Play in European Club Football Competitions. , 2018, , 135-157.		9
47	Anisotropy and phonon modes from analysis of the dielectric function tensor and the inverse dielectric function tensor of monoclinic yttrium orthosilicate. <i>Physical Review B</i> , 2018, 97, .	1.1	15
48	Elevated temperature dependence of the anisotropic visible-to-ultraviolet dielectric function of monoclinic $\text{In}_2\text{-Ga}_2\text{O}_3$ . <i>Applied Physics Letters</i> , 2018, 112, .	1.5	14
49	Salt Sensitivity of the Thermoresponsive Behavior of PNIPAAm Brushes. <i>Langmuir</i> , 2018, 34, 2448-2454.	1.6	13
50	Electron effective mass in Sn-doped monoclinic single crystal $\text{In}_2\text{-gallium oxide}$ determined by mid-infrared optical Hall effect. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	43
51	Electrical and material properties of hydrothermally grown single crystal (111) $\text{UO}_2$ . <i>European Physical Journal B</i> , 2018, 91, 1.	0.6	6
52	Advanced Terahertz Frequency-Domain Ellipsometry Instrumentation for <i>In Situ</i> and <i>Ex Situ</i> Applications. <i>IEEE Transactions on Terahertz Science and Technology</i> , 2018, 8, 257-270.	2.0	42
53	Adsorption and decontamination of $\text{I}^\pm$ -synuclein from medically and environmentally-relevant surfaces. <i>Colloids and Surfaces B: Biointerfaces</i> , 2018, 166, 98-107.	2.5	7
54	Critical-point model dielectric function analysis of $\text{WO}_3$ thin films deposited by atomic layer deposition techniques. <i>Journal of Applied Physics</i> , 2018, 124, .	1.1	5

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55	Composition-Dependent Charge Transport in Boron Carbides Alloyed with Aromatics: Plasma Enhanced Chemical Vapor Deposition Aniline/Orthocarborane Films. <i>Langmuir</i> , 2018, 34, 12007-12016.	1.6	7
56	Detection of Organic Attachment onto Highly Ordered Three-Dimensional Nanostructure Thin Films by Generalized Ellipsometry and Quartz Crystal Microbalance with Dissipation Techniques. <i>Springer Series in Surface Sciences</i> , 2018, , 225-245.	0.3	1
57	Biofunctionalization of Titanium Substrates using Nanoscale Polymer Brushes with Cell Adhesion Peptides. <i>Journal of Physical Chemistry B</i> , 2018, 122, 6543-6550.	1.2	16
58	Combined quartz crystal microbalance with dissipation (QCM-D) and generalized ellipsometry (GE) to characterize the deposition of titanium dioxide nanoparticles on model rough surfaces. <i>Journal of Hazardous Materials</i> , 2017, 322, 118-128.	6.5	23
59	Effects of annealing and conformal alumina passivation on anisotropy and hysteresis of magneto-optical properties of cobalt slanted columnar thin films. <i>Applied Surface Science</i> , 2017, 421, 320-324.	3.1	4
60	Multi-scale investigation of interface properties, stacking order and decoupling of few layer graphene on C-face 4H-SiC. <i>Carbon</i> , 2017, 116, 722-732.	5.4	23
61	Quartz crystal microbalance with coupled spectroscopic ellipsometry-study of temperature-responsive polymer brush systems. <i>Applied Surface Science</i> , 2017, 421, 843-851.	3.1	31
62	Structural and optical properties of alumina passivated amorphous Si slanted columnar thin films during electrochemical Li-ion intercalation and deintercalation observed by in situ generalized spectroscopic ellipsometry. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017, 35, 031401.	0.6	0
63	Infrared dielectric functions, phonon modes, and free-charge carrier properties of high-Al-content Al <sub>x</sub> Ga <sub>1-x</sub> N alloys determined by mid infrared spectroscopic ellipsometry and optical Hall effect. <i>Journal of Applied Physics</i> , 2017, 121, .	1.1	14
64	Control of slanting angle, porosity, and anisotropic optical constants of slanted columnar thin films via in situ nucleation layer tailoring. <i>Applied Surface Science</i> , 2017, 421, 766-771.	3.1	3
65	Screening effects in metal sculptured thin films studied with terahertz Mueller matrix ellipsometry. <i>Applied Surface Science</i> , 2017, 421, 513-517.	3.1	4
66	Optical and structural properties of cobalt-permalloy slanted columnar heterostructure thin films. <i>Applied Surface Science</i> , 2017, 421, 783-787.	3.1	4
67	Anisotropy, phonon modes, and lattice anharmonicity from dielectric function tensor analysis of monoclinic cadmium tungstate. <i>Physical Review B</i> , 2017, 95, .	1.1	22
68	In-situ terahertz optical Hall effect measurements of ambient effects on free charge carrier properties of epitaxial graphene. <i>Scientific Reports</i> , 2017, 7, 5151.	1.6	23
69	Multiple-layered effective medium approximation approach to modeling environmental effects on alumina passivated highly porous silicon nanostructured thin films measured by in-situ Mueller matrix ellipsometry. <i>Applied Surface Science</i> , 2017, 421, 663-666.	3.1	7
70	Cavity-enhanced optical Hall effect in epitaxial graphene detected at terahertz frequencies. <i>Applied Surface Science</i> , 2017, 421, 357-360.	3.1	8
71	Band-to-band transitions, selection rules, effective mass, and excitonic contributions in monoclinic $\text{CdWO}_4$ . <i>Physical Review B</i> , 2017, 96, .	1.1	17
72	The guardians of European football: UEFA Financial Fair Play and the career of social problems. <i>European Journal for Sport and Society</i> , 2016, 13, 296-324.	1.2	8

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73	Decoupling and ordering of multilayer graphene on C-face 3C-SiC(111). Applied Physics Letters, 2016, 109, .	1.5	10
74	Anisotropic contrast optical microscope. Review of Scientific Instruments, 2016, 87, 113701.	0.6	10
75	Anisotropy, band-to-band transitions, phonon modes, and oxidation properties of cobalt-oxide core-shell slanted columnar thin films. Applied Physics Letters, 2016, 108, .	1.5	12
76	Ion beam sputtering of Ti: Influence of process parameters on angular and energy distribution of sputtered and backscattered particles. Nuclear Instruments & Methods in Physics Research B, 2016, 385, 30-39.	0.6	23
77	Solution-stable anisotropic carbon nanotube/graphene hybrids based on slanted columnar thin films for chemical sensing. RSC Advances, 2016, 6, 63235-63240.	1.7	3
78	Optical Hall effect "model description: tutorial. Journal of the Optical Society of America A: Optics and Image Science, and Vision, 2016, 33, 1553.	0.8	40
79	Coordinate-Invariant Lyddane-Sachs-Teller Relationship for Polar Vibrations in Materials with Monoclinic and Triclinic Crystal Systems. Physical Review Letters, 2016, 117, 215502.	2.9	30
80	Anisotropy, phonon modes, and free charge carrier parameters in monoclinic $\text{Al}_2\text{O}_3$ -gallium oxide single crystals. Physical Review B, 2016, 93, .	1.1	147
81	(N)Olympia in Germany? An analysis of the referendum against Munich 2022. Sportwissenschaft, 2016, 46, 15-24.	0.6	34
82	Optical anisotropy of porous polymer film with inverse slanted nanocolumnar structure revealed via generalized spectroscopic ellipsometry. Applied Physics Letters, 2015, 107, .	1.5	6
83	Infrared dielectric functions and optical phonons of wurtzite $\text{Al}_2\text{O}_3$ . Journal of Applied Physics, 2015, 118, 033102.	1.5	12
84	Use of precisely sculptured thin film (STF) substrates with generalized ellipsometry to determine spatial distribution of adsorbed fibronectin to nanostructured columnar topographies and effect on cell adhesion. Acta Biomaterialia, 2015, 18, 88-99.	4.1	17
85	The retention of liquid by columnar nanostructured surfaces during quartz crystal microbalance measurements and the effects of adsorption thereon. Journal of Colloid and Interface Science, 2015, 455, 226-235.	5.0	6
86	Structural properties and dielectric function of graphene grown by high-temperature sublimation on 4H-SiC(000-1). Journal of Applied Physics, 2015, 117, .	1.1	16
87	Cavity-enhanced optical Hall effect in two-dimensional free charge carrier gases detected at terahertz frequencies. Optics Letters, 2015, 40, 2688.	1.7	19
88	Anisotropic magneto-optical hysteresis of permalloy slanted columnar thin films determined by vector magneto-optical generalized ellipsometry. Applied Physics Letters, 2015, 106, .	1.5	7
89	Structural and optical properties of cobalt slanted nanopillars conformally coated with few-layer graphene. Applied Physics Letters, 2015, 106, 231901.	1.5	8
90	Investigation of Bovine Serum Albumin (BSA) Attachment onto Self-Assembled Monolayers (SAMs) Using Combinatorial Quartz Crystal Microbalance with Dissipation (QCM-D) and Spectroscopic Ellipsometry (SE). PLoS ONE, 2015, 10, e0141282.	1.1	154

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91	“Classical” doping, financial doping and beyond: UEFA’s financial fair play as a policy of anti-doping. International Journal of Sport Policy and Politics, 2014, , 1-24.	1.0	13
92	Effect of Mg doping on the structural and free-charge carrier properties of InN films. Journal of Applied Physics, 2014, 115, 163504.	1.1	16
93	Assessing structural, free-charge carrier, and phonon properties of mixed-phase epitaxial films: The case of InN. Physical Review B, 2014, 90, .	1.1	15
94	Free-charge carrier parameters of n-type, p-type and compensated InN:Mg determined by infrared spectroscopic ellipsometry. Thin Solid Films, 2014, 571, 384-388.	0.8	4
95	Morphological and electronic properties of epitaxial graphene on SiC. Physica B: Condensed Matter, 2014, 439, 54-59.	1.3	29
96	Combined QCM-D/GE as a tool to characterize stimuli-responsive swelling of and protein adsorption on polymer brushes grafted onto 3D-nanostructures. Analytical and Bioanalytical Chemistry, 2014, 406, 7233-7242.	1.9	20
97	Invited Article: An integrated mid-infrared, far-infrared, and terahertz optical Hall effect instrument. Review of Scientific Instruments, 2014, 85, 071301.	0.6	45
98	Dynamic analysis of DNA nanoparticle immobilization to model biomaterial substrates using combinatorial spectroscopic ellipsometry and quartz crystal microbalance with dissipation. Thin Solid Films, 2014, 571, 637-643.	0.8	8
99	Potential agency problems in European club football? The case of UEFA Financial Fair Play. Sport, Business and Management, 2014, 4, 336-350.	0.7	26
100	Detection of Organic Attachment onto Highly Ordered Three-Dimensional Nanostructure Thin Films by Generalized Ellipsometry and Quartz Crystal Microbalance with Dissipation Techniques. Springer Series in Surface Sciences, 2014, , 135-154.	0.3	2
101	Generalized ellipsometry effective medium approximation analysis approach for porous slanted columnar thin films infiltrated with polymer. Applied Physics Letters, 2013, 103, 111906.	1.5	13
102	Infrared dielectric anisotropy and phonon modes of rutile TiO <sub>2</sub> . Journal of Applied Physics, 2013, 113, 164102.	1.1	35
103	Anisotropic Bruggeman effective medium approaches for slanted columnar thin films. Journal of Applied Physics, 2013, 114, .	1.1	80
104	Infrared to vacuum-ultraviolet ellipsometry and optical Hall-effect study of free-charge carrier parameters in Mg-doped InN. Journal of Applied Physics, 2013, 113, .	1.1	22
105	Vector magneto-optical generalized ellipsometry for sculptured thin films. Applied Physics Letters, 2013, 102, .	1.5	14
106	Generalized Ellipsometry Characterization of Sculptured Thin Films Made by Glancing Angle Deposition. , 2013, , 341-410.		7
107	Slanted Columnar Thin Films Prepared by Glancing Angle Deposition Functionalized with Polyacrylic Acid Polymer Brushes. Journal of Physical Chemistry C, 2013, 117, 13971-13980.	1.5	29
108	THz Generalized Ellipsometry Characterization of Highly-Ordered Three-Dimensional Nanostructures. , 2013, , 411-428.		1

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109	Large-area microfocal spectroscopic ellipsometry mapping of thickness and electronic properties of epitaxial graphene on Si- and C-face of 3C-SiC(111). Applied Physics Letters, 2013, 102, .	1.5	28
110	A Model Dielectric Function for Graphene from the Infrared to the Ultraviolet. Materials Research Society Symposia Proceedings, 2013, 1505, 1.	0.1	0
111	Optical Hall effect measurement of coupled phonon mode - Landau Level transitions in epitaxial Graphene on silicon carbide. Materials Research Society Symposia Proceedings, 2013, 1505, 1.	0.1	1
112	Polarization Selection Rules for Inter-Landau-Level Transitions in Epitaxial Graphene Revealed by the Infrared Optical Hall Effect. Physical Review Letters, 2013, 111, 077402.	2.9	18
113	Electron effective mass in Al <sub>0.72</sub> Ga <sub>0.28</sub> N alloys determined by mid-infrared optical Hall effect. Applied Physics Letters, 2013, 103, .	1.5	30
114	In Situ Synthesis of Palladium Nanoparticles in Polymer Brushes Followed by QCM-DE Coupled with Spectroscopic Ellipsometry. Particle and Particle Systems Characterization, 2013, 30, 931-935.	1.2	7
115	Metal slanted columnar thin film THz optical sensors. Materials Research Society Symposia Proceedings, 2012, 1409, 61.	0.1	10
116	Vector Magneto-Optical Generalized Ellipsometry on Passivated Permalloy Slanted Columnar Thin Films. Materials Research Society Symposia Proceedings, 2012, 1408, 23.	0.1	3
117	Infrared ellipsometry and near-infrared-to-vacuum-ultraviolet ellipsometry study of free-charge carrier properties in In-polar p-type InN. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	0
118	Generalized ellipsometry in-situ quantification of organic adsorbate attachment within slanted columnar thin films. Optics Express, 2012, 20, 5419.	1.7	33
119	Direct graphene growth on Co <sub>3</sub> O <sub>4</sub> (111) by molecular beam epitaxy. Journal of Physics Condensed Matter, 2012, 24, 072201.	0.7	18
120	Optical properties of cobalt slanted columnar thin films passivated by atomic layer deposition. Applied Physics Letters, 2012, 100, .	1.5	43
121	Aging Effects of As-deposited and Passivated Cobalt Slanted Columnar Thin Films. Materials Research Society Symposia Proceedings, 2012, 1409, 7.	0.1	2
122	Spectroscopic Mapping Ellipsometry of Graphene Grown on 3C SiC. Materials Research Society Symposia Proceedings, 2012, 1407, 99.	0.1	1
123	Temperature dependent effective mass in AlGaIn/GaN high electron mobility transistor structures. Applied Physics Letters, 2012, 101, .	1.5	44
124	Visible to vacuum ultraviolet dielectric functions of epitaxial graphene on 3C and 4H SiC polytypes determined by spectroscopic ellipsometry. Applied Physics Letters, 2012, 101, .	1.5	33
125	Combined optical and acoustical method for determination of thickness and porosity of transparent organic layers below the ultra-thin film limit. Review of Scientific Instruments, 2011, 82, 103111.	0.6	41
126	Terahertz ellipsometry and terahertz optical-Hall effect. Thin Solid Films, 2011, 519, 2593-2600.	0.8	46



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127	Micelle-assisted bilayer formation of cetyltrimethylammonium bromide thin films studied with combinatorial spectroscopic ellipsometry and quartz crystal microbalance techniques. Thin Solid Films, 2011, 519, 2821-2824.	0.8	13
128	Virtual separation approach to study porous ultra-thin films by combined spectroscopic ellipsometry and quartz crystal microbalance methods. Thin Solid Films, 2011, 519, 2772-2776.	0.8	30
129	In-situ monitoring of alkanethiol self-assembled monolayer chemisorption with combined spectroscopic ellipsometry and quartz crystal microbalance techniques. Thin Solid Films, 2011, 519, 2817-2820.	0.8	30
130	Temperature dependent model dielectric function of highly disordered Ga <sub>0.52</sub> In <sub>0.48</sub> P. Thin Solid Films, 2011, 519, 2859-2862.	0.8	0
131	Terahertz optical-Hall effect for multiple valley band materials: n-type silicon. Thin Solid Films, 2011, 519, 2613-2616.	0.8	11
132	Free-charge carrier profile of iso- and aniso-type Si homojunctions determined by terahertz and mid-infrared ellipsometry. Thin Solid Films, 2011, 519, 2604-2607.	0.8	5
133	Optical properties of GaAs <sub>0.9-x</sub> N <sub>x</sub> Sb <sub>0.1</sub> alloy films studied by spectroscopic ellipsometry. Thin Solid Films, 2011, 519, 2838-2842.	0.8	4
134	Optical properties of hybrid titanium chevron sculptured thin films coated with a semiconducting polymer. Thin Solid Films, 2011, 519, 2645-2649.	0.8	10
135	Hole-channel conductivity in epitaxial graphene determined by terahertz optical-Hall effect and midinfrared ellipsometry. Applied Physics Letters, 2011, 98, .	1.5	39
136	Terahertz optical-Hall effect characterization of two-dimensional electron gas properties in AlGa <sub>N</sub> /Ga <sub>N</sub> high electron mobility transistor structures. Applied Physics Letters, 2011, 98, .	1.5	25
137	THz dielectric anisotropy of metal slanted columnar thin films. Applied Physics Letters, 2011, 99, 081903.	1.5	33
138	Spectroscopic ellipsometry characterization of Si <sub>N</sub> <sub>x</sub> antireflection films on textured multicrystalline and monocrystalline silicon solar cells. Thin Solid Films, 2010, 518, 1830-1834.	0.8	24
139	Voigt effect measurement on PLD grown NiO thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 334-337.	0.8	3
140	Variable-wavelength frequency-domain terahertz ellipsometry. Review of Scientific Instruments, 2010, 81, 023101.	0.6	73
141	Magneto-optical properties of cobalt slanted columnar thin films. Applied Physics Letters, 2010, 96, .	1.5	22
142	Hydrogen in InN: A ubiquitous phenomenon in molecular beam epitaxy grown material. Applied Physics Letters, 2010, 96, .	1.5	36
143	<i>Ab initio</i> calculations and ellipsometry measurements of the optical properties of the layered semiconductor $\ln_{1-x}\text{Mn}_x\text{N}$ . Physical Review B, 2010, 81, .	1.1	20
144	Interface polarization coupling in piezoelectric-semiconductor ferroelectric heterostructures. Physical Review B, 2010, 81, .	1.1	38

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145	Protein adsorption on and swelling of polyelectrolyte brushes: A simultaneous ellipsometry-quartz crystal microbalance study. <i>Biointerphases</i> , 2010, 5, 159-167.	0.6	94
146	Optical, structural, and magnetic properties of cobalt nanostructure thin films. <i>Journal of Applied Physics</i> , 2009, 105, .	1.1	66
147	Resistive hysteresis and interface charge coupling in BaTiO <sub>3</sub> -ZnO heterostructures. <i>Applied Physics Letters</i> , 2009, 94, 142904.	1.5	51
148	Annealing effects on the optical properties of semiconducting boron carbide. <i>Journal of Applied Physics</i> , 2009, 106, .	1.1	18
149	Characterizing antireflection coatings on textured monocrystalline silicon with Spectroscopic Ellipsometry. , 2009, , .		1
150	Materials Characterization using THz Ellipsometry. <i>Materials Research Society Symposia Proceedings</i> , 2009, 1163, 8041.	0.1	0
151	Electrical properties of ZnO/BaTiO <sub>3</sub> /ZnO heterostructures with asymmetric interface charge distribution. <i>Applied Physics Letters</i> , 2009, 95, .	1.5	22
152	Electron accumulation at nonpolar and semipolar surfaces of wurtzite InN from generalized infrared ellipsometry. <i>Applied Physics Letters</i> , 2009, 95, 202103.	1.5	24
153	Role of impurities and dislocations for the unintentional n-type conductivity in InN. <i>Physica B: Condensed Matter</i> , 2009, 404, 4476-4481.	1.3	15
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